



FEATURES

- Circular active area
- Ideal for electron detection
- 100% internal QE
- High speed
- Grid lines 5 microns, Pitch 100 microns
- RoHS and REACH compliant

RoHS

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

| PARAMETERS | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|----------------------------------|------------------------------|-----|------|-----|-----------------|
| Active Area | Ø5.01mm | | 19.7 | | mm ² |
| Responsivity, \mathcal{R} | (see graphs on next page) | | | | A/W |
| Reverse Breakdown Voltage, V_R | $I_R = 1\mu A$ | 160 | | | Volts |
| Capacitance, C | $V_R = 0V$ | | 200 | 800 | pF |
| Rise Time | $R_L = 50\Omega, V_R = 150V$ | | | 2 | nsec |
| Dark Current | $V_R = 150V$ | | | 100 | nA |

THERMAL PARAMETERS

| STORAGE AND OPERATING TEMPERATURE RANGE | |
|---|---------------------------|
| Ambient ¹ | -10° TO 40°C ¹ |
| Nitrogen or Vacuum | -20°C TO 80°C |
| Lead Soldering Temperature ² | 260°C |

¹Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

